DG EB

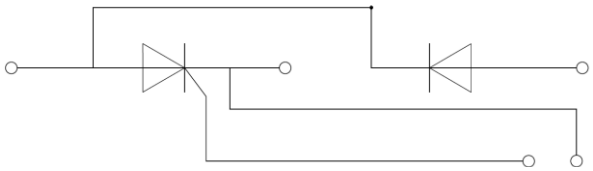
b c G f

J M g g

J g	P f	O c
℃		

fc c





f G g g L c a

J g	cc	M g f	P f	O c
	℃			
				℃
				℃

f c f b c c

J g	cc	M g f	P f			O c
			Gc (	(	G (	
	℃					
	℃					
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	℃					

I c a C g c

c	G ec a	J e a	ab	C	J

c f f c f b g f b c c

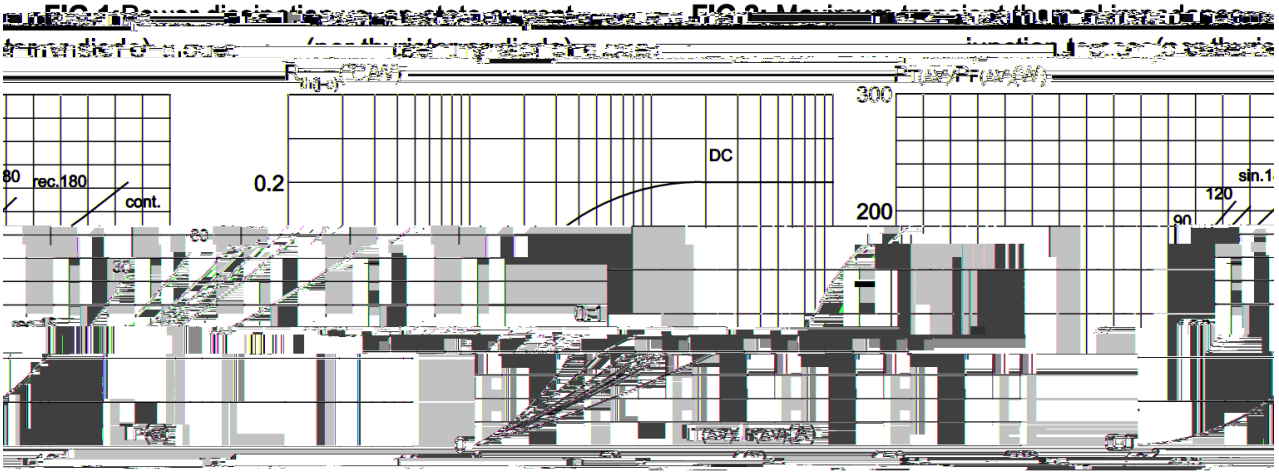


FIG.3: Forward characteristics
(per thyristor or diode)

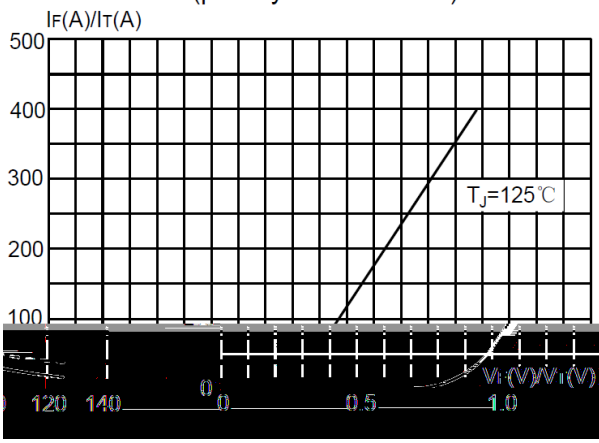
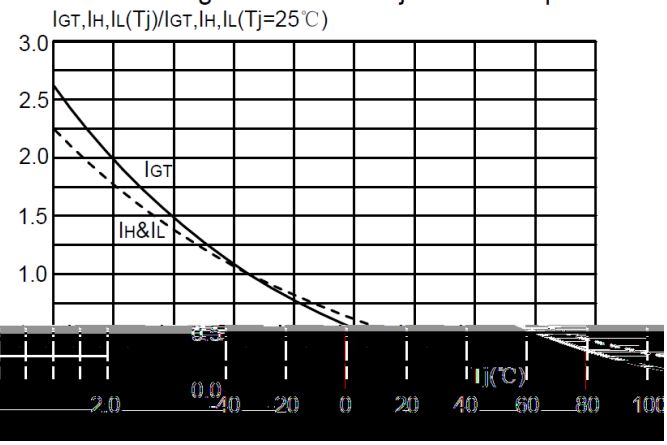
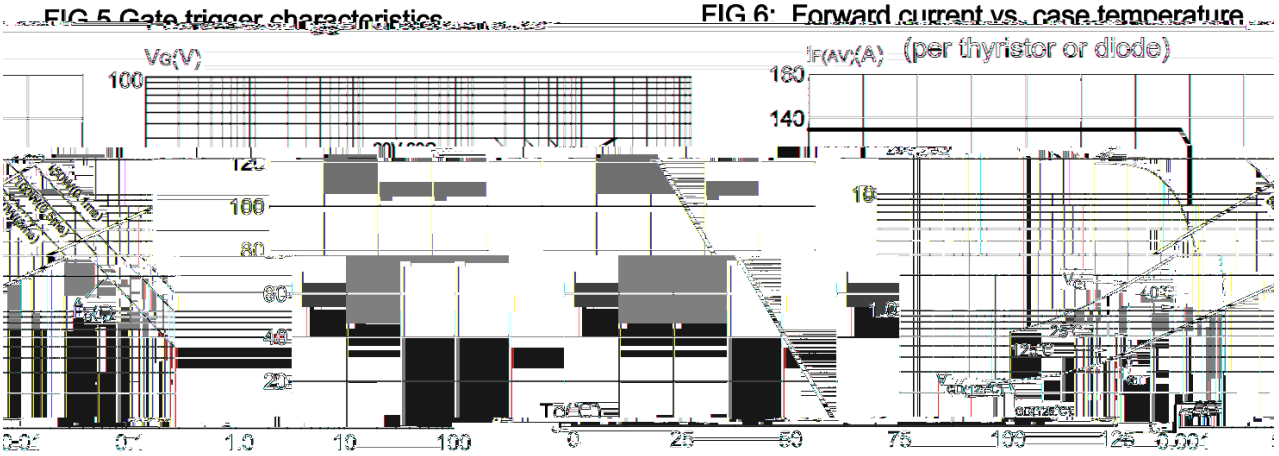
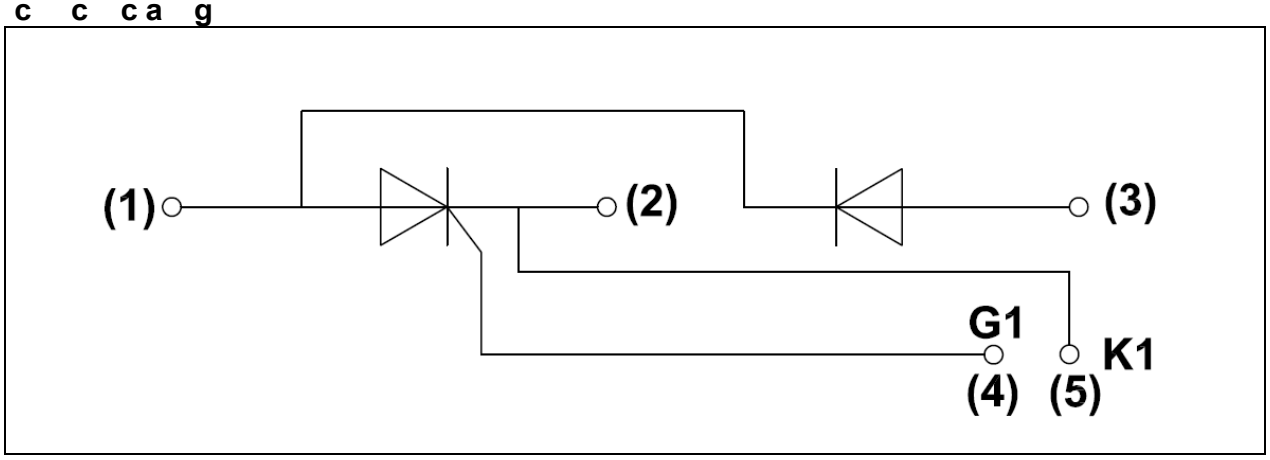


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

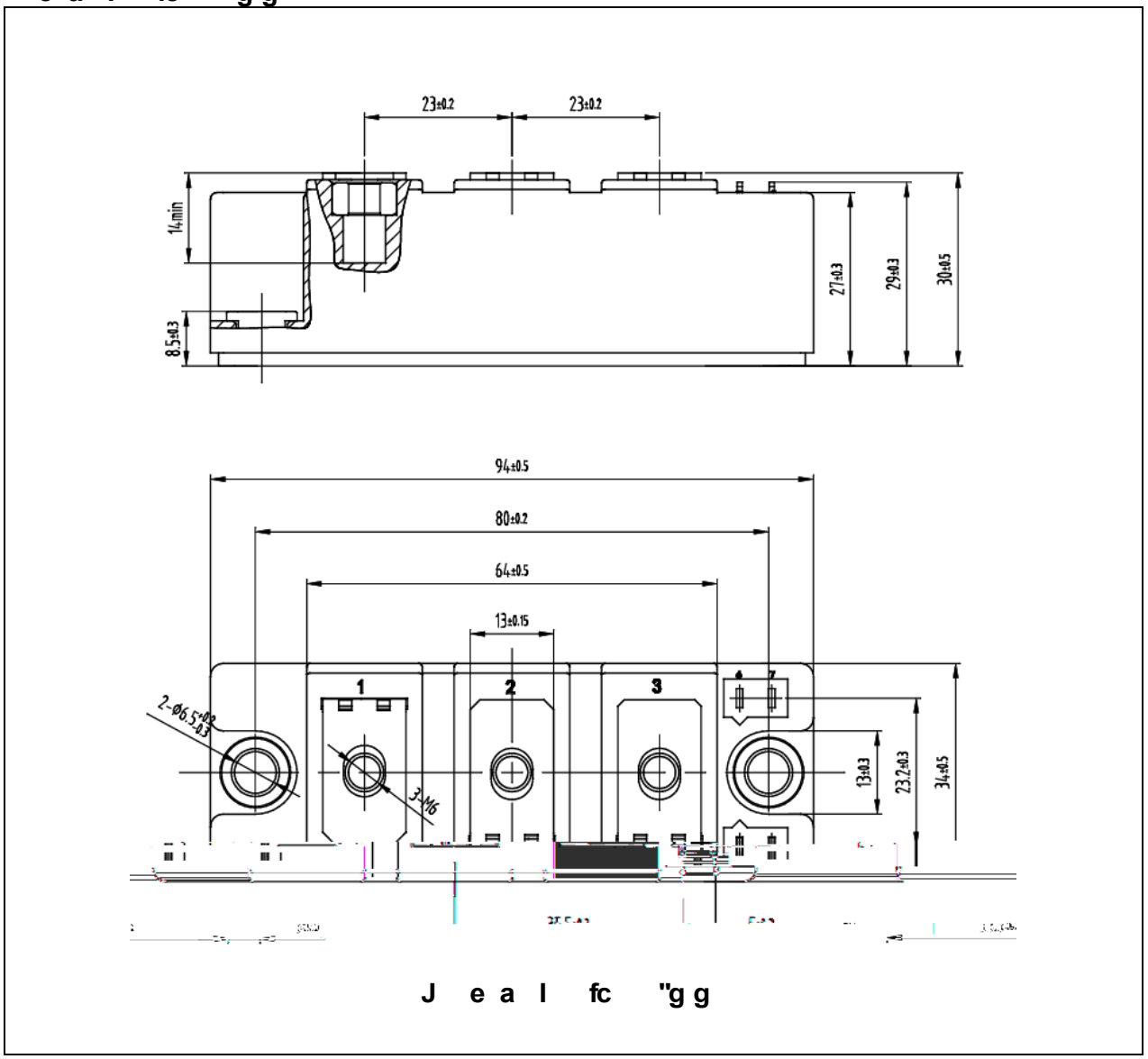




c c c a g



J e a l fc "g g



J e a l fc "g g